

IN THE CLAIMS:

Amend claims 2-8 and 13-17, add claims 18-21 and cancel claim 9 as follows:

1. (Cancelled)

2. (Currently Amended) The integrated circuit of claim 16, wherein the ~~raised-stamped~~ pedestals have sidewalls with an angle (α) greater than 45 degrees with respect to a plane of the carrier device die paddle.

3. (Currently Amended) The integrated circuit of claim 16, wherein the ~~raised-stamped~~ pedestals each have a plane surface which is parallel to a ~~plane of the chip~~ connection area plane of the carrier device and each has an area for connection of a single bonding wire.

4. (Currently Amended) The integrated circuit of claim 16, wherein a height of each of the ~~raised-stamped~~ pedestals lies in the range between 1/10 and 1.5 times of a height of the semiconductor die.

5. (Currently Amended) The integrated circuit of claim 16, wherein a height of each of the ~~stamped~~ raised pedestals lies in the range from 1/5 to twice a material thickness (h) of the carrier device.

6. (Currently Amended) The integrated circuit of claim 16, wherein the ~~raised-stamped~~ pedestals each represent a local deformation of the carrier device which is formed by a punch or a bending-off device.

7. (Currently Amended) The integrated circuit of claim 16, wherein the ~~raised~~-stamped pedestals are formed by application of material to the carrier device.

8. (Currently Amended) The integrated circuit of claim 16, wherein a silver or gold finish is applied to the ~~raised~~-stamped pedestals.

9. (Cancelled)

10. (Cancelled)

11. (Cancelled)

12. (Cancelled)

13. (Currently Amended) The integrated circuit of claim 17, where the ~~raised~~-stamped pedestals make an angle (α) greater than 45 degrees with the plane of the carrier device at all ~~sideswall~~sidewalls, with the sidewalls having rounded junctions parallel to the plane of the carrier device or being rounded as a whole.

14. (Currently Amended) The integrated circuit of claim 17, where the height of the ~~raised~~-stamped pedestals lies in the range between 1/10 of the die height and the die height itself.

15. (Currently Amended) The integrated circuit of claim ~~44~~16, where only in the areas of the raised-stamped pedestals, a finish, particularly silver or gold, is provided for bondability.

16. (Currently Amended) An integrated circuit, comprising:

a semiconductor die;

a carrier device comprising a die paddle onto which the die is attached and a plurality of metallic leads each comprising an inner lead portion that extends to an outer lead portion, where a plurality of stamped pedestals are arranged on the carrier device exteriorly surrounding and adjacent to the die paddle, where the carrier device, the die paddle and the stamped pedestals form a single piece unitary structure;

a first bond wire extending from the die to a first of the plurality of stamped pedestals, and a second bond wire extending from the first of the plurality of stamped pedestals to an inner lead portion; and

a package that encapsulates the semiconductor die, the die paddle, the first and second bond wires and the inner lead portions.

17. (Currently Amended) An integrated circuit, comprising:

a semiconductor die;

a metallic carrier device comprising a planar surface onto which the die is attached and a plurality of metallic leads each comprising an inner lead portion that extends to an outer lead portion, where a plurality of stamped pedestals are arranged on the carrier device exteriorly surrounding and adjacent to the planar surface, where the carrier device, the die paddle and the stamped pedestals form a single piece unitary structure; and

a first bond wire extending from the die to a first of the plurality of stamped pedestals, and a second bond wire extending from the first of the plurality of stamped pedestals to an inner lead portion.

18. (New) An integrated circuit, comprising:

a non-conductive carrier device having a plurality of integrally raised pedestals, at least one of the pedestals having a bonding pad;

a semiconductor die coupled to the non-conductive carrier device, where the carrier device, the die paddle and the stamped pedestals form a single piece unitary structure; and

a first bonding wire electrically coupling the semiconductor die to the bonding pad.

19. (New) The integrated circuit of claim 18, further comprising

a lead; and

a second bonding wire electrically coupling the bonding pad to the lead.

20. (New) The integrated circuit of claim 19, further comprising a package that encapsulates the semiconductor die, the first and the second bonding wires and a portion of the lead.

21. (New) The integrated circuit of claim 18, wherein the bonding pad is composed of at least one of gold and silver.